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NATIONAL STANDARD OF THE PEOPLE'S REPUBLIC OF CHINA

GB/T 6217-2026

Replacing GB/T 6217-1998

Discrete semiconductor devices - Blank detail specification for low power bipolar transistors

半导体分立器件 小功率双极型晶体管空白详细规范

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Standardization Administration of the PRC

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1 Scope

GB/T 6217-2026 is the Chinese national standard covering the blank form a manufacturer fills in to specify a small signal transistor - the parameters that must be declared, their test conditions and the sequence in which they are set out, so that two datasheets can be compared line by line. It replaces GB/T 6217-1998 and has been in force since 1 October 2026, with the high power version GB/T 7576-2026. It was issued on 31 March 2026 and takes effect on 1 October 2026, replacing GB/T 6217-1998. This page is published from the official record of the 2026 edition; the clause text of a standard this recent is not yet in circulation, and the figures, limits and tables it contains are those of the document itself, delivered in full with the English translation.

This document defines low-power bipolar transistors (hereinafter referred to as devices) (including high- and low-frequency low-power bipolar transistors and low-power bipolar transistors). Technical requirements and quality assurance regulations for polarized switching transistors. This document applies to the development of detailed specifications for low-power bipolar transistors.

3 Terms and Definitions

This document does not contain any terms or definitions that need to be defined.

4 Requirements

4.1 General Requirements This document should be used in conjunction with GB/T 4023.1-2026.

4.2 Structure and Shape Detailed specifications should provide the basic structure of the device (including the semiconductor materials used, chip fabrication structure, chip bonding or sintering process, and bonding). The material, diameter and quantity of the wire) and its

shape (including the package shape, lead material and coating, dimensions, etc.). Dimension Code. When the dimensions of a device are listed in GB/T 7581, the dimension code of the device should be given. Outline drawing. When the outline dimensions of a device are not listed in GB/T 7581, a detailed outline drawing of the device should be provided. Lead identification. A lead arrangement diagram should be specified.

4.3 Maximum Ratings and Main Electrical Characteristics

4.3.1 Maximum Rated Value The maximum rated parameters of the device shall conform to the specifications in Table

1.Unless otherwise specified, these rated parameters shall apply throughout the operating temperature range. For internal use only.

4.3.2 Electrical Characteristics The electrical characteristics of the device shall conform to the specifications in Table 2 (unless otherwise specified, Ta = 25°C, and other environmental conditions shall conform to GB/T 4589.1-2006). (As specified in 4.1). Inspection requirements are detailed in Chapter 4.

4.3.3 Electrical parameter curves The detailed specifications should provide key electrical parameter curves for the device, including total power dissipation versus temperature derating curves.

4.4 Quality Assessment Categories and Quality Grades Detailed specifications should provide the quality assessment category and quality grade of the device, see GB/T 4589.1-2006 and GB/T 4023.1-2026.

4.5 Marking

4.5.1 Markings on the device The markings on the device shall comply with the provisions of GB/T 4023.1-2026.

4.5.2 Markings on the packaging box The markings on the packaging box should include at least.

---Manufacturer's trademark;

---Contact information for the manufacturer.

4.6 Model Naming Model naming should comply with the provisions of GB/T 249.

5 Inspection

5.1 Screening The screening should comply with the provisions of section

6.5 and Table 3 of GB/T 4023.1-2026.

5.2 Quality Consistency Inspection

5.2.1 General Rules Quality consistency inspection shall comply with the provisions of

6.6 and Tables 4 to 6 of GB/T 4023.1-2026.

5.2.2 Group A Test Group A testing is conducted batch-by-batch, and the specific testing items are shown in Table

4.Structural similarity should not be used as a substitute for Group A testing.

5.2.3 Group B Test Group B testing is conducted batch-by-batch; specific testing items are shown in Table

5.Group B testing allows the use of test data from structurally similar devices. To make a substitution. GB/T 6217-2026. Blank Detailed Specification for Small Power Bipolar Transistors, Discrete Semiconductor Devices ICS

42 National Standards of the People's Republic of China Replaces GB/T 6217-1998 and GB/T 6218-1996 Semiconductor discrete devices Low-power bipolar transistor blank detailed specification Published on 2026-03-

31 Implemented on October 1, 2026 State Administration for Market Regulation The State Administration for Standardization issued a statement.